



YJG70G06A

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	70A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	7.5 mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	9.5 mohm
100% EAS Tested	
100% V_{DS} Tested	

General Description

Split Gate Trench MOSFET technology
Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

DC-DC Converters
Power management functions
Industrial and Motor Drive application

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

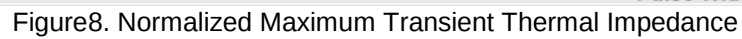
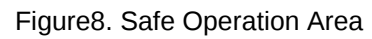
Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	60	V
Gate-source Voltage	V		



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Electrical Characteristics ($T_J=25$ unless otherwise noted)

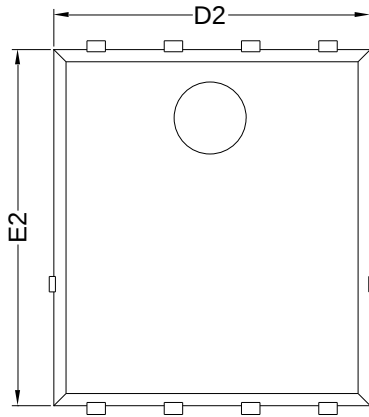
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1	



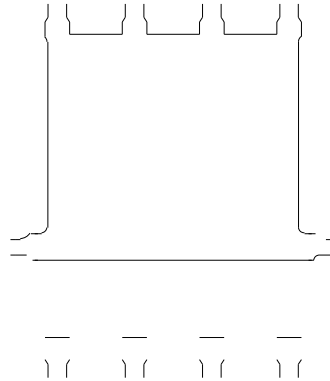


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PDFN5060-8L-B-1.1MM Package information



Top View



Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.

